

SOT-23 M M P $\int \tilde{\omega} \underline{z} \cdot \gamma$

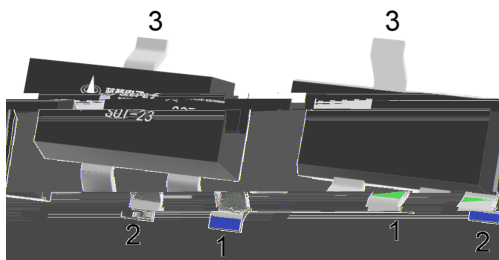
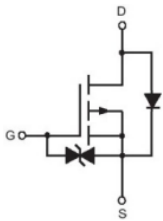
P-CHANNEL MOSFET in a SOT-23 Plastic Package.

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Low threshold voltage, Direct interface to C-MOS, TTL etc, High-speed switching,ESD Improved Capability 1000V, high current, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

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Line current interrupter in telephone sets, Relay, High speed and line transformer drivers, Meet the stringent requirements of automotive applications.

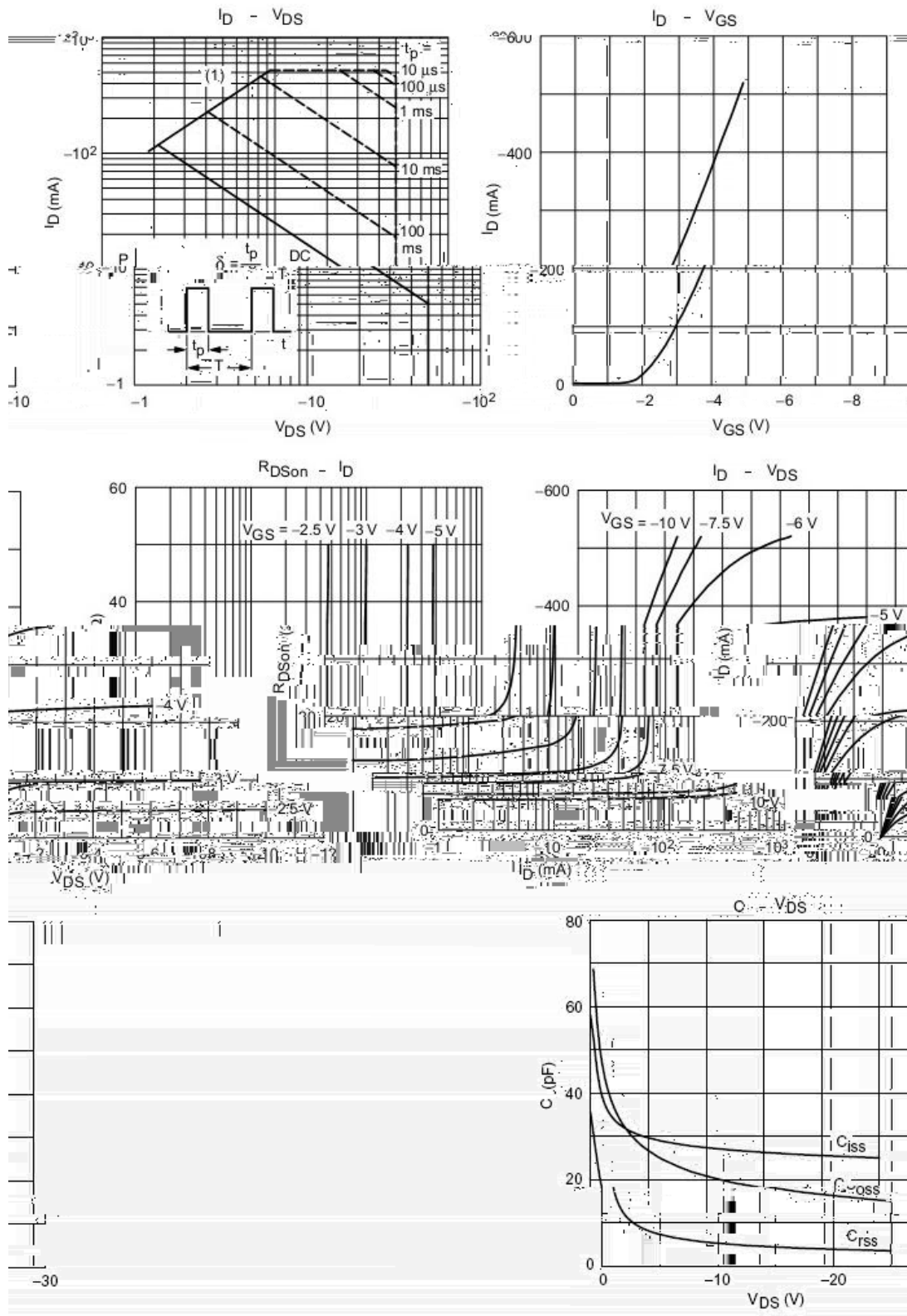
PIN1 $\times$ GPIN 2 χ SPIN 3 χ D

Marking	QSP
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Rev.A Mar.-2023

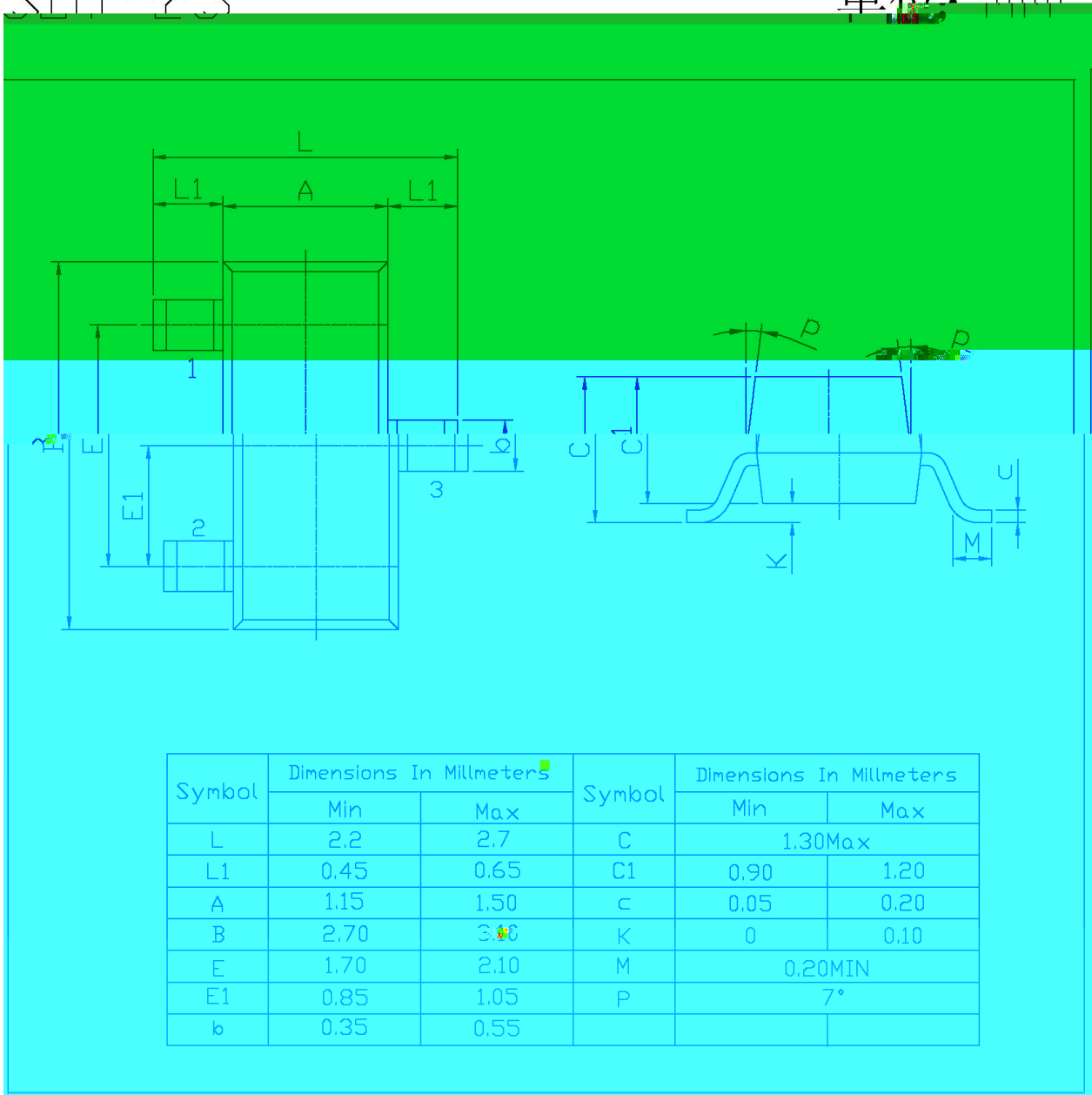
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-50	V
Drain Current – Continuous	I_D	-130	mA
Peak Drain Current	I_{DM}	-520	mA
Gate-Source Voltage	V_{GS}	± 20	V
Thermal Resistance, Junction-to-Ambient	R_{JA}	500	/W
Storage Temperature Range	T_{stg}	-65 to 150	
Junction Temperature Range	T_j	150	

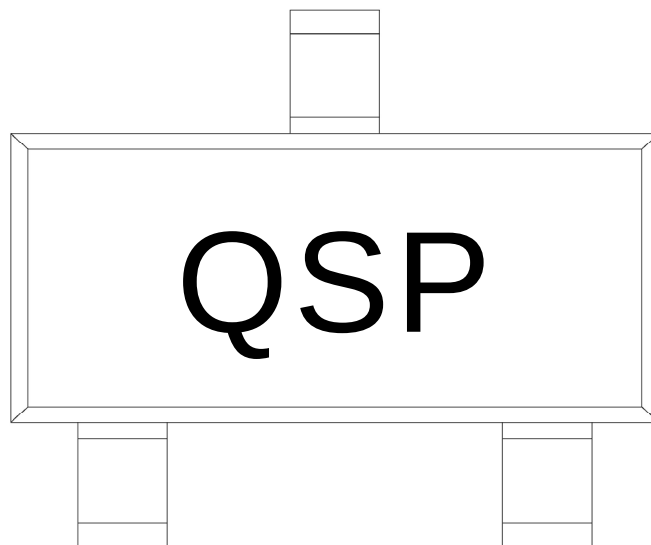
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	V_{DSS}	$V_{GS}=0V$ $I_D=-10\text{ A}$	-50			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\text{ A}$	-0.8		-2.0	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V$ $V_{DS}=-40V$			-100	nA
		$V_{GS}=0V$ $V_{DS}=-50V$			-10	nA



SOT-23

单位: mm





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SP X Ƨ Ƨ Ƨ Ƨ

Note:

Q: Automobile halogen-free product Code

SP: Product Type.

Temperature Profile for IR Reflow Soldering(Pb-Free)

- ” X
- 1 150 ℃~200 ℃ 60 ℃~120sec;

2 255 ℃±5 ℃ 5 ℃~0.5sec;

3 2~10 ℃/sec.

Note:

1.Preheating:150~200 ℃ , Time:60~120sec.

2.Peak Temp.:255 ℃±5 ℃ , Duration:5 ℃~0.5sec.

3.Cooling Speed: 2~10 ℃ /sec.

260 ℃±5 ℃ 10 ℃~1 sec.

Temp.:260 ℃±5 ℃ Time:10 ℃~1 sec

/ REEL

Package Type